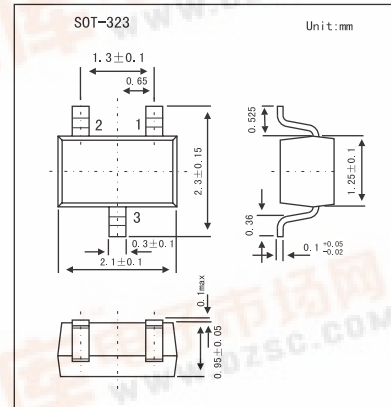


SMD Type Diodes

Silicon Schottky Diode
BAT17-04W, BAT17-05W, BAT17-06W

Features

- For mixer applications in VHF/UHF range
- For high-speed switching application



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	4	V
Forward current	I _F	130	mA
Total power dissipation	P _{tot}	150	mW
Junction temperature	T _j	150	°C
Operating temperature range	T _{op}	-55 to +125	°C
Storage temperature	T _{stg}	-55 to +150	°C
Junction - soldering point(Note 1)	R _{thJS}	≤ 390	K/W

Note

1. For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V _(BR)	I _(BR) = 10 μA	4			V
Reverse current	I _R	V _R = 3 V			0.25	μA
		V _R = 4 V			10	
		V _R = 3 V, T _A = 60°C			1.25	
Forward voltage	V _F	I _F = 0.1 mA	200	275	350	mV
		I _F = 1 mA	250	340	450	
		I _F = 10 mA	350	425	600	
Forward voltage matching(Note 1)	ΔV _F	I _F = 1 mA			20	mV
Diode capacitance	C _T	V _R = 0, f = 1 MHz	0.4	0.55	0.75	pF
Differential forward resistance	R _F	I _F = 5 mA, f = 10 KHz		8	15	Ω

Note

1. ΔV_F is the difference between lowest and highest V_F in multiple diode component.

Marking

Type	BAT17-04W	BAT17-05W	BAT17-06W
Marking	54S	55S	56S

